

74AHC2G00-Q100; 74AHCT2G00-Q100

Dual 2-input NAND gate

Rev. 1 — 21 March 2013

Product data sheet

1. General description

The 74AHC2G00-Q100; 74AHCT2G00-Q100 are high-speed Si-gate CMOS devices. They provide two 2-input NAND gates.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

The AHCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$
- Symmetrical output impedance
- High noise immunity
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200\text{ pF}$, $R = 0\text{ }\Omega$)
- Low power dissipation
- Balanced propagation delays
- Multiple package options

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AHC2G00DP-Q100 74AHCT2G00DP-Q100	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74AHC2G00DC-Q100 74AHCT2G00DC-Q100	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1



4. Marking

Table 2. Marking

Type number	Marking code ^[1]
74AHC2G00DP-Q100	A00
74AHCT2G00DP-Q100	C00
74AHC2G00DC-Q100	A00
74AHCT2G00DC-Q100	C00

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

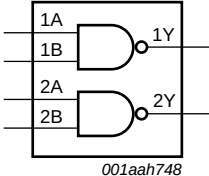


Fig 1. Logic symbol

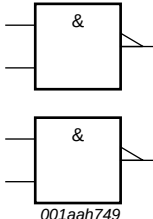


Fig 2. IEC logic symbol

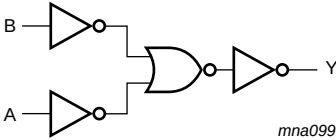


Fig 3. Logic diagram (one gate)

6. Pinning information

6.1 Pinning

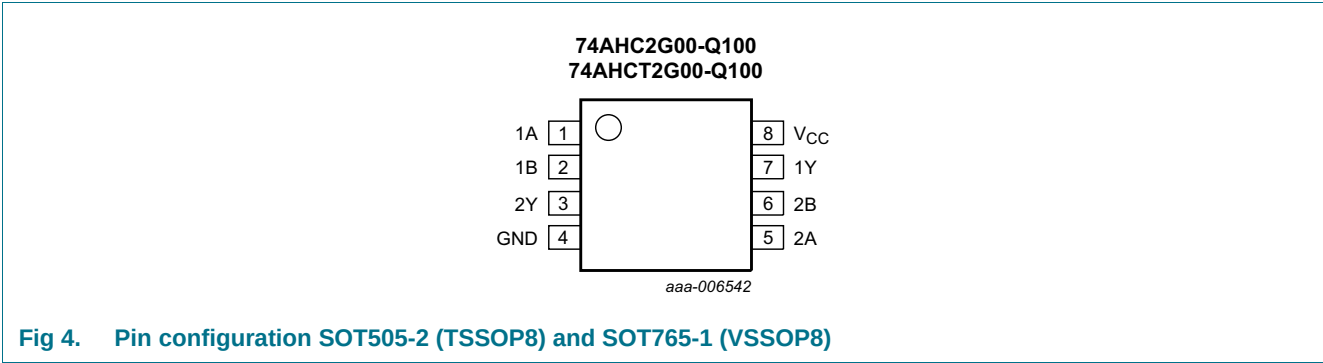


Fig 4. Pin configuration SOT505-2 (TSSOP8) and SOT765-1 (VSSOP8)

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A, 2A	1, 5	data input
1B, 2B	2, 6	data input
GND	4	ground (0 V)
1Y, 2Y	7, 3	data output
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table^[1]

Input		Output
nA	nB	nY
L	L	H
L	H	H
H	L	H
H	H	L

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
V_I	input voltage		-0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5$ V	[1] -20	-	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	[1] -	±20	mA
I_O	output current	-0.5 V < V_O < $V_{CC} + 0.5$ V	-	±25	mA
I_{CC}	supply current		-	75	mA
I_{GND}	ground current		-75	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[2] -	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.
For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74AHC2G00-Q100			74AHCT2G00-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
V_I	input voltage		0	-	5.5	0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 3.3$ V ± 0.3 V	-	-	100	-	-	-	ns/V
		$V_{CC} = 5.0$ V ± 0.5 V	-	-	20	-	-	20	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74AHC2G00-Q100										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
		V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V

Table 7. Static characteristics ...continued
 Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = –50 µA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = –50 µA; V _{CC} = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I _O = –50 µA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = –4.0 mA; V _{CC} = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
		I _O = –8.0 mA; V _{CC} = 4.5 V	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 50 µA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 µA; V _{CC} = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 µA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I _O = 8.0 mA; V _{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	10	-	10	-	40	µA
C _I	input capacitance		-	1.5	10	-	10	-	10	pF
74AHCT2G00-Q100										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = –50 µA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = –8.0 mA	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = 50 µA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	1.0	-	10	-	40	µA
ΔI _{CC}	additional supply current	per input pin; V _I = 3.4 V; other inputs at V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
C _I	input capacitance		-	1.5	10	-	10	-	10	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics

$GND = 0\text{ V}$; for test circuit see [Figure 6](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74AHC2G00-Q100										
t _{pd}	propagation delay	nA, nB to nY; see Figure 5 [1]								
		V _{CC} = 3.0 V to 3.6 V [2]								
		C _L = 15 pF	-	4.5	7.9	1.0	9.5	1.0	10.5	ns
		C _L = 50 pF	-	6.5	11.4	1.0	13.0	1.0	14.5	ns
		V _{CC} = 4.5 V to 5.5 V [3]								
		C _L = 15 pF	-	3.5	5.5	1.0	6.5	1.0	7.0	ns
		C _L = 50 pF	-	4.9	7.5	1.0	8.5	1.0	9.5	ns
C _{PD}	power dissipation capacitance	per buffer; [4] C _L = 50 pF; f _i = 1 MHz; V _I = GND to V _{CC}	-	17	-	-	-	-	-	pF
74AHCT2G00-Q100										
t _{pd}	propagation delay	nA, nB to nY; see Figure 5 [1]								
		V _{CC} = 4.5 V to 5.5 V [3]								
		C _L = 15 pF	1.0	3.6	6.2	1.0	7.1	1.0	8.0	ns
		C _L = 50 pF	1.0	5.0	7.9	1.0	9.0	1.0	10.0	ns
C _{PD}	power dissipation capacitance	per buffer; [4] C _L = 50 pF; f _i = 1 MHz; V _I = GND to V _{CC}	-	18	-	-	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

[2] Typical values are measured at $V_{CC} = 3.3\text{ V}$.

[3] Typical values are measured at $V_{CC} = 5.0\text{ V}$.

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

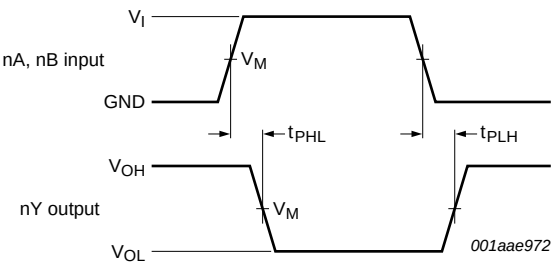
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms

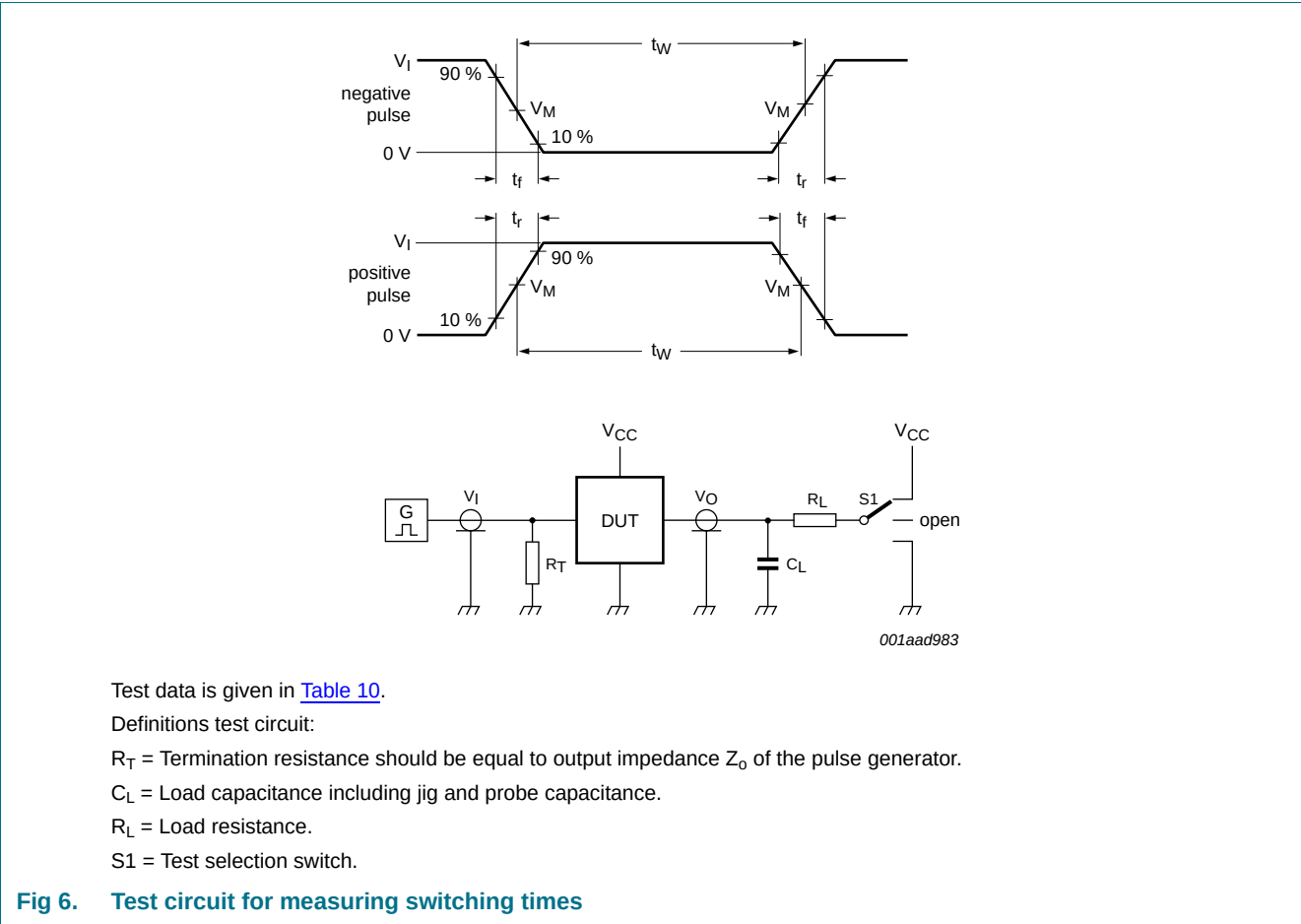


Measurement points are given in [Table 9](#).
Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 5. The input (nA and nB) to output (nY) propagation delays.

Table 9. Measurement points

Type	Input V_M	Output V_M
74AHC2G00-Q100	$0.5V_{CC}$	$0.5V_{CC}$
74AHCT2G00-Q100	1.5 V	$0.5V_{CC}$



Test data is given in [Table 10](#).

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

$S1$ = Test selection switch.

Fig 6. Test circuit for measuring switching times

Table 10. Test data

Type	Input		Load		S1 position
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}
74AHC2G00-Q100	V_{CC}	$\leq 3 \text{ ns}$	15 pF, 50 pF	1 k Ω	open
74AHCT2G00-Q100	3 V	$\leq 3 \text{ ns}$	15 pF, 50 pF	1 k Ω	open

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

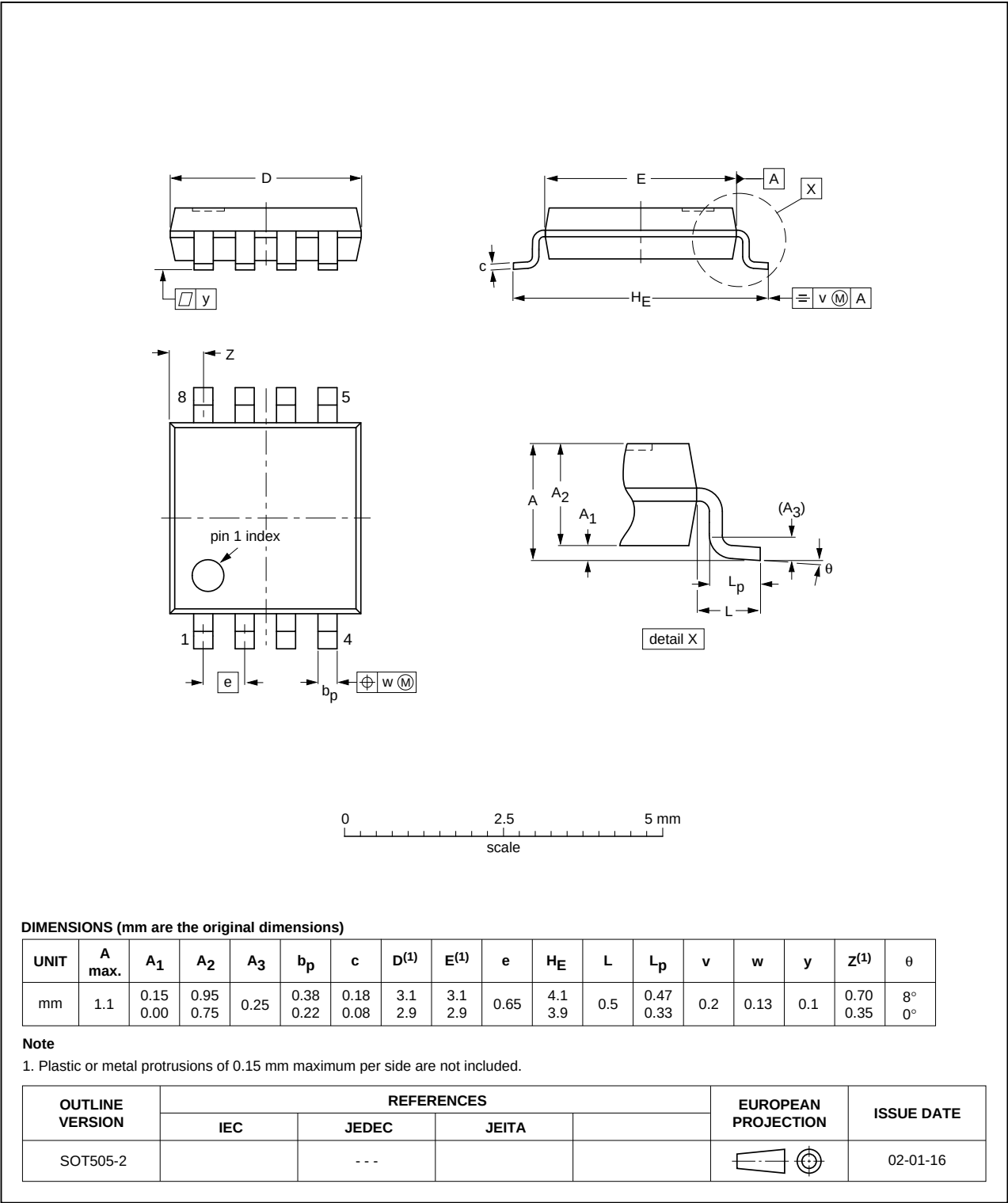


Fig 7. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

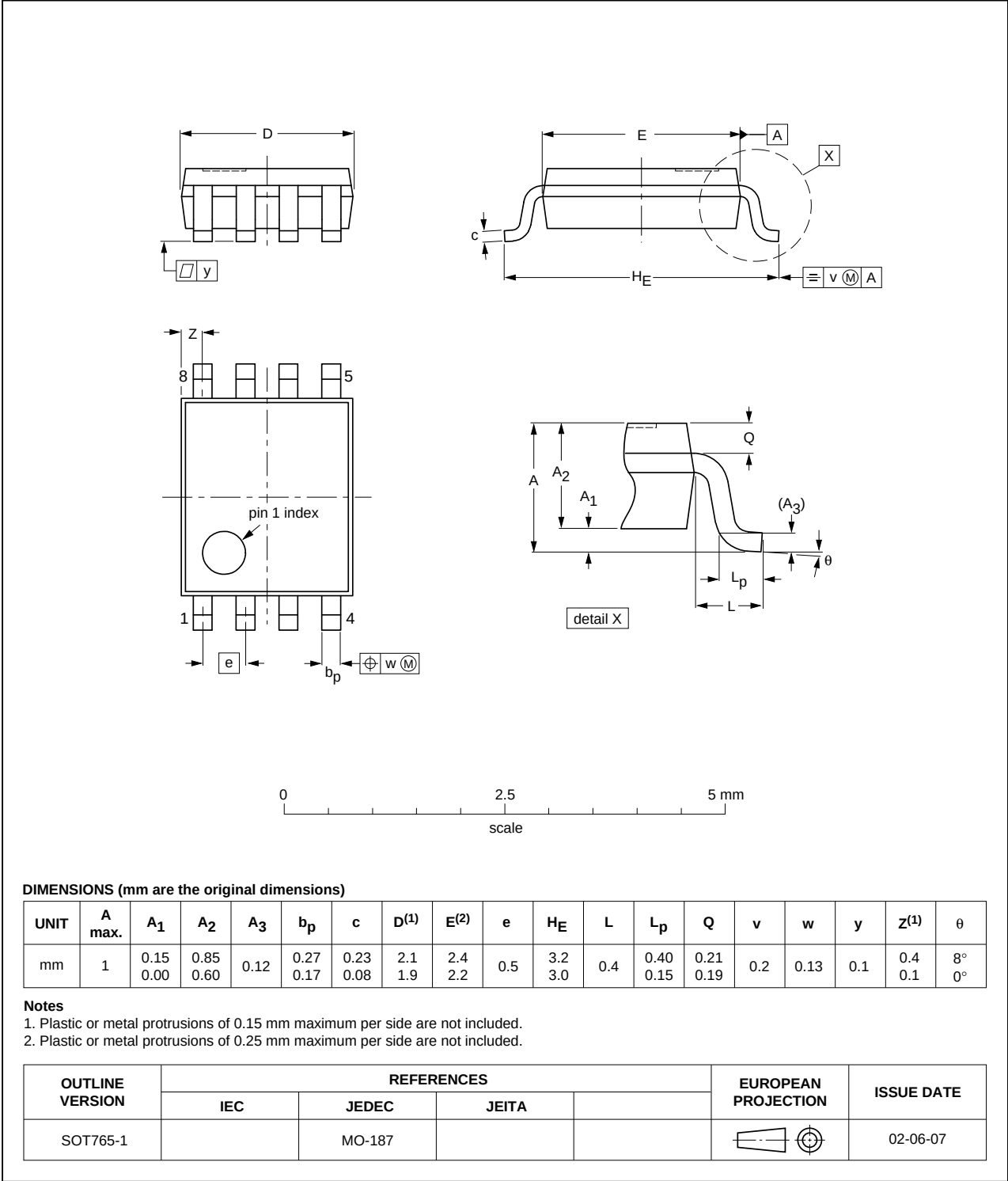


Fig 8. Package outline SOT765-1 (VSSOP8)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic
MIL	Military

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT2G00_Q100 v.1	20130321	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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